

Description

The HXY2333AI uses advanced trench technology

to provide excellent $R_{\text{DS}(\text{ON})}$, This device is suitable

for use as a load switch or in PWM applications.

D G G

SOT-23

General Features

 $V_{DS} = -18V, I_{D} = -6.5A$

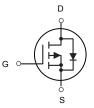
 $R_{DS(ON)}$ < 28m Ω @ V_{GS} =-4.5V

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY2333AI	SOT-23	20P07	3000

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	-18	V
V _G s	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous	-6.5	А
Ідм	Drain Current-Pulsed (Note 1)	-15	А
P _D	Maximum Power Dissipation	2	W
Тл,Тѕтв	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	74	°C/W

HXY2333AI

Electrical Characteristics (T_A=25°C unless otherwise noted)

Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-	-18	•	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V,V _{GS} =0V	-	-	-1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±8V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)	On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA	-0.45	-0.7	-1.0	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4.1A	-	20	28	mΩ	
Diam-Source On-State Resistance		V _{GS} =-2.5V, I _D =-3A	-	27	36		
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-3.5A	-	8.5	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	\/ - 4\/\/ -0\/	-	980	-	PF	
Output Capacitance	C _{oss}	V_{DS} =-4V, V_{GS} =0V, F=1.0MHz	-	450	-	PF	
Reverse Transfer Capacitance	C _{rss}	F-1.UWIFIZ	-	250	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	12	-	nS	
Turn-on Rise Time	t _r	V_{DD} =-4V, I_{D} =-3.3A ,	-	35	-	nS	
Turn-Off Delay Time	t _{d(off)}	R_{L} =-1.2 Ω , V_{GEN} =-4.5 V , R_{g} =1 Ω	-	30	-	nS	
Turn-Off Fall Time	t _f		-	10	-	nS	
Total Gate Charge	Qg		-	7.8	-	nC	
Gate-Source Charge	Q_gs	V_{DS} =-4V, I_{D} =-4.1A, V_{GS} =-4.5V	-	1.2	-	nC	
Gate-Drain Charge	Q_{gd}		-	1.6	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-1.6A	-	-	-1.2	V	
Diode Forward Current (Note 2)	Is		-	-	1.6	Α	

Notes:

- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Characteristics

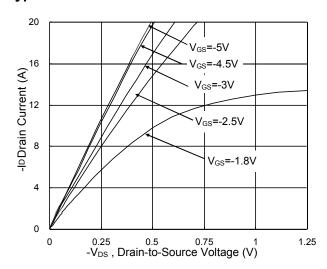


Fig.1 Typical Output Characteristics

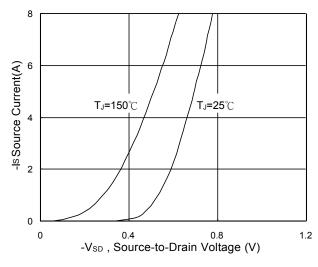


Fig.3 Forward Characteristics Of Reverse

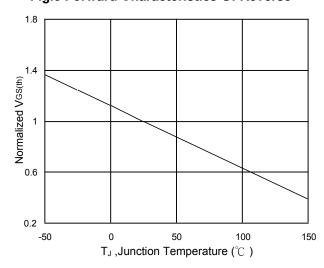


Fig.5 Normalized $V_{\text{GS(th)}}$ vs. T_{J}

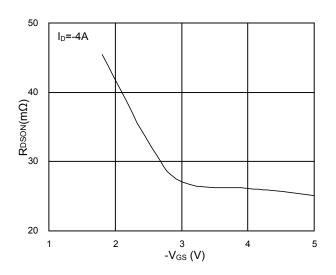


Fig.2 On-Resistance vs. Gate-Source

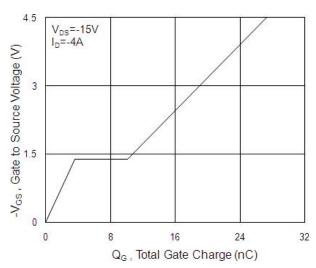


Fig.4 Gate-Charge Characteristics

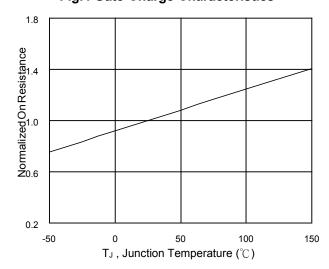
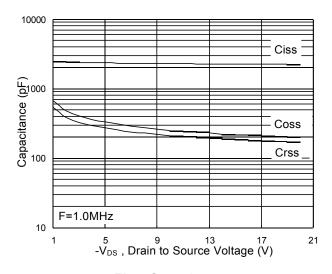


Fig.6 Normalized R_{DSON} vs. T_J



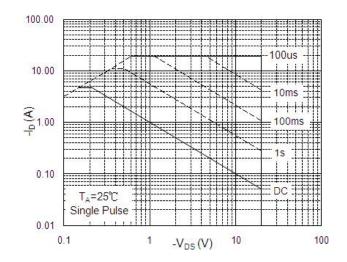


Fig.7 Capacitance

Fig.8 Safe Operating Area

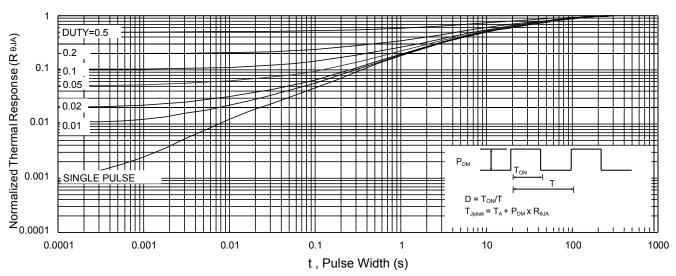
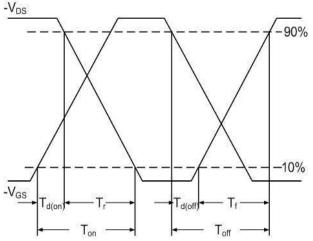
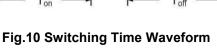


Fig.9 Normalized Maximum Transient Thermal Impedance





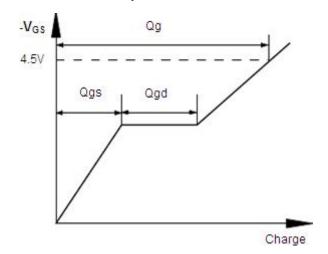
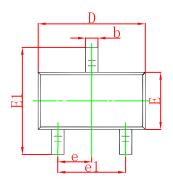
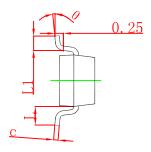


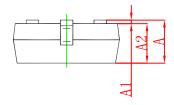
Fig.11 Gate Charge Waveform



SOT-23 Package Outline Dimensions

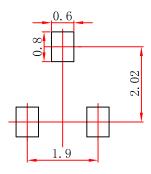






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note: 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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